

Transient Voltage Suppressors for ESD Protection

General Description

The LESD8D5.0CT5G is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

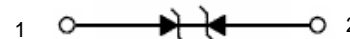
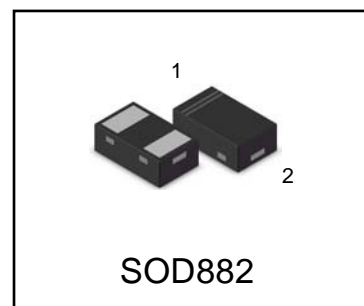
Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

Features

- Small Body Outline Dimensions
- Low Body Height
- Peak Power up to 150 Watts @ 8 x 20 μ s Pulse
- Low Leakage current
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

LESD8D5.0CT5G
S-LESD8D5.0CT5G



Ordering information

Device	Marking	Shipping
LESD8D5.0CT1G S-LESD8D5.0CT1G	C	5000/Tape&Reel
LESD8D5.0CT3G S-LESD8D5.0CT3G	C	8000/Tape&Reel
LESD8D5.0CT5G S-LESD8D5.0CT5G	C	10000/Tape&Reel

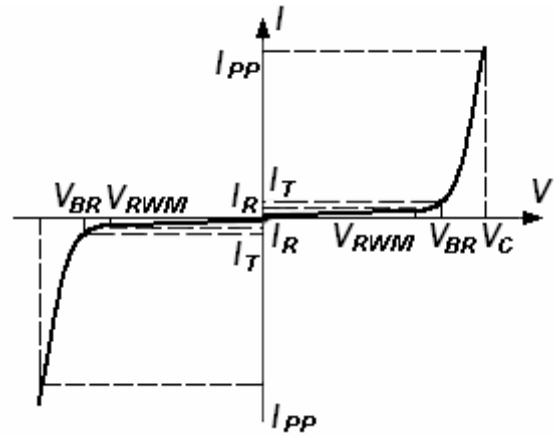
Absolute Ratings (T_{amb}=25°C)

Symbol	Parameter	Value	Units
P _{PP}	Peak Pulse Power (t _p = 8/20 μ s)	150	W
T _L	Maximum lead temperature for soldering during 10s	260	°C
T _{stg}	Storage Temperature Range	-55 to +155	°C
T _{op}	Operating Temperature Range	-40 to +125	°C
T _j	Maximum junction temperature	150	°C
	IEC61000-4-2 (ESD) air discharge	\pm 15	KV
	IEC61000-4-4 (EFT) contact discharge	\pm 8	KV
	ESD Voltage Per Human Body Model	40	A
		16	KV

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Electrical Parameter

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
I_T	Test Current
V_{BR}	Breakdown Voltage @ I_T



Electrical Characteristics Ratings at 25°C ambient temperature unless otherwise specified. VF = 0.9V at IF = 10mA

Device	V_{RWM} (V)	I_{R1} (uA) @ V_{RWM}	I_{R2} (uA) @ $V_R=3.5V$	V_{BR} (V) @ I_T (Note 1)	I_T	V_C (V) @ $I_{PP}=5 A^*$	V_C (V) @ Max I_{PP}^*	I_{PP} (A)*	P_{PK} (W)*	C (pF)
	Max	Max	Max	Min	mA	Typ	Max	Max	Max	Typ
LESD8D5.0CT5G	5.0	0.5	0.3	5.6	1.0	11.6	18.6	9.4	174	15

*Surge current waveform per Figure 1.

1. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.

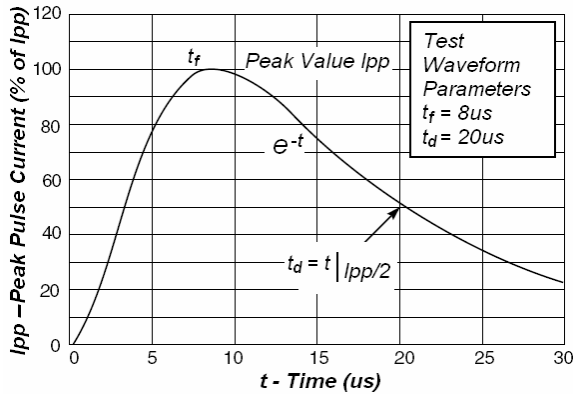


Fig1. Pulse Waveform

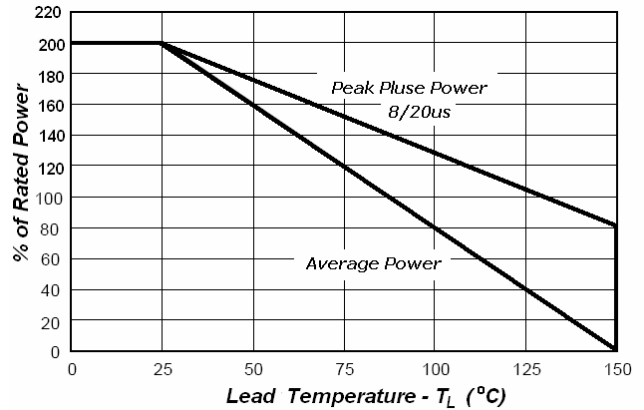


Fig2. Power Derating Curve

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DIMENSION OUTLINE:

Unit:mm

